



# **DMP2018LFK-7 Information**



For Reference Only

Part Number DMP2018LFK-7
Manufacturer Diodes Incorporated

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET P-CH 20V 9.2A 6-DFN

Package 6-PowerUDFN

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **DMP2018LFK-7 Specifications**

Manufacturer Part NumberDMP2018LFK-7ManufacturerDiodes IncorporatedCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackage6-PowerUDFNSeries-FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C9.2A (Ta)Drive Voltage (Max Rds On, Min Rds On)1.5V, 4.5VVgs(th) (Max) @ Id1.2V @ 200μAGate Charge (Qg) (Max) @ Vgs113nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4748pF @ 10VVgs (Max)±12VFET Feature-Power Dissipation (Max)1W (Ta)Rds On (Max) @ Id, Vgs16 mOhm @ 3.6A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageU-DFN2523-6Package / Case6-PowerUDFNReport errors?		
Category  Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single  Package 6-PowerUDFN  Series - FET Type P-Channel Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) 20V  Current - Continuous Drain (Id) @ 25°C 9.2A (Ta)  Drive Voltage (Max Rds On, Min Rds On) 1.5V, 4.5V  Vgs(th) (Max) @ Id 1.2V @ 200µA  Gate Charge (Qg) (Max) @ Vgs 113nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds 4748pF @ 10V  Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 16 mOhm @ 3.6A, 4.5V  Operating Temperature Surface Mount Supplier Device Package Package / Case 6-PowerUDFN	Manufacturer Part Number	DMP2018LFK-7
Package       6-PowerUDFN         Series       -         FET Type       P-Channel         Technology       MOSFET (Metal Oxide)         Drain to Source Voltage (Vdss)       20V         Current - Continuous Drain (Id) @ 25°C       9.2A (Ta)         Drive Voltage (Max Rds On, Min Rds On)       1.5V, 4.5V         Vgs(th) (Max) @ Id       1.2V @ 200μA         Gate Charge (Qg) (Max) @ Vgs       113nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       4748pF @ 10V         Vgs (Max)       ±12V         FET Feature       -         Power Dissipation (Max)       1W (Ta)         Rds On (Max) @ Id, Vgs       16 mOhm @ 3.6A, 4.5V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Surface Mount         Supplier Device Package       U-DFN2523-6         Package / Case       6-PowerUDFN	Manufacturer	Diodes Incorporated
Package         6-PowerUDFN           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         20V           Current - Continuous Drain (Id) @ 25°C         9.2A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         1.5V, 4.5V           Vgs(th) (Max) @ Id         1.2V @ 200µA           Gate Charge (Qg) (Max) @ Vgs         113nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         4748pF @ 10V           Vgs (Max)         ±12V           FET Feature         -           Power Dissipation (Max)         1W (Ta)           Rds On (Max) @ Id, Vgs         16 mOhm @ 3.6A, 4.5V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         U-DFN2523-6           Package / Case         6-PowerUDFN	Category	Discrete Semiconductor Products
Series-FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C9.2A (Ta)Drive Voltage (Max Rds On, Min Rds On)1.5V, 4.5VVgs(th) (Max) @ Id1.2V @ 200μAGate Charge (Qg) (Max) @ Vgs113nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4748pF @ 10VVgs (Max)±12VFET Feature-Power Dissipation (Max)1W (Ta)Rds On (Max) @ Id, Vgs16 mOhm @ 3.6A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageU-DFN2523-6Package / Case6-PowerUDFN		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 9.2A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.5V, 4.5V Vgs(th) (Max) @ Id 1.2V @ 200µA Gate Charge (Qg) (Max) @ Vgs 113nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4748pF @ 10V Vgs (Max) ±12V FET Feature - Power Dissipation (Max) 1W (Ta) Rds On (Max) @ Id, Vgs 16 mOhm @ 3.6A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package U-DFN2523-6 Package / Case 6-PowerUDFN	Package	6-PowerUDFN
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 9.2A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.5V, 4.5V Vgs(th) (Max) @ Id 1.2V @ 200µA Gate Charge (Qg) (Max) @ Vgs 113nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4748pF @ 10V Vgs (Max)  FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 16 mOhm @ 3.6A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 6-PowerUDFN	Series	-
Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C9.2A (Ta)Drive Voltage (Max Rds On, Min Rds On)1.5V, 4.5VVgs(th) (Max) @ Id1.2V @ 200μAGate Charge (Qg) (Max) @ Vgs113nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4748pF @ 10VVgs (Max)±12VFET Feature-Power Dissipation (Max)1W (Ta)Rds On (Max) @ Id, Vgs16 mOhm @ 3.6A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageU-DFN2523-6Package / Case6-PowerUDFN	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  1.5V, 4.5V  Vgs(th) (Max) @ Id  1.2V @ 200µA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  #12V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  16 mOhm @ 3.6A, 4.5V  Operating Temperature  Surplier Device Package  Package / Case  9.2A (Ta)  1.5V, 4.5V  9.2A (Ta)  1.5V, 4.5V  10V  10V  10V  10N  10V  10V  10V  10	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  1.2V @ 200μA  Gate Charge (Qg) (Max) @ Vgs  113nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ±12V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  16 mOhm @ 3.6A, 4.5V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  6-PowerUDFN	Drain to Source Voltage (Vdss)	20V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  Package / Case  1.2V @ 200μA  1.3nC @ 10V  113nC @ 10V  4748pF @ 10V  50V  50V  4748pF @ 10V  50V  50V  50V  60POWEUDFN	Current - Continuous Drain (Id) @ 25°C	9.2A (Ta)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  4748pF @ 10V  Vgs (Max)  ±12V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  16 mOhm @ 3.6A, 4.5V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  6-PowerUDFN	Drive Voltage (Max Rds On, Min Rds On)	1.5V, 4.5V
Input Capacitance (Ciss) (Max) @ Vds 4748pF @ 10V  Vgs (Max) ±12V  FET Feature -  Power Dissipation (Max) 1W (Ta)  Rds On (Max) @ Id, Vgs 16 mOhm @ 3.6A, 4.5V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Surface Mount  Supplier Device Package U-DFN2523-6  Package / Case 6-PowerUDFN	Vgs(th) (Max) @ Id	1.2V @ 200μA
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Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  16 mOhm @ 3.6A, 4.5V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  U-DFN2523-6  Package / Case  6-PowerUDFN	Vgs (Max)	±12V
Rds On (Max) @ Id, Vgs16 mOhm @ 3.6A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageU-DFN2523-6Package / Case6-PowerUDFN	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  U-DFN2523-6  Package / Case  6-PowerUDFN	Power Dissipation (Max)	1W (Ta)
Mounting Type Surface Mount Supplier Device Package U-DFN2523-6 Package / Case 6-PowerUDFN	Rds On (Max) @ Id, Vgs	16 mOhm @ 3.6A, 4.5V
Supplier Device Package U-DFN2523-6 Package / Case 6-PowerUDFN	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 6-PowerUDFN	Mounting Type	Surface Mount
	Supplier Device Package	U-DFN2523-6
Report errors?	Package / Case	6-PowerUDFN
		Report errors?

### **DMP2018LFK-7 Guarantees**



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# **DMP2018LFK-7 Payment Methods**



















# **DMP2018LFK-7 Shipping Methods**













If you have any question about DMP2018LFK-7, please do not hesitate to contact us!

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